

	Hit s	Search Text	DBs
12	12	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same (interference or (diffract\$4 near9 grat\$4) or beam\$2splitt\$4 or diffract\$4 or (interferometric near6 lithograph\$3))) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical or conventional)) and ((second near12 (photoresist or resist) near6 (layer or coat\$4 or deposit\$4 or film)) and ((third or multiple) near9 (expos\$4 or irradiat\$4 or illuminat\$4)) and pitch\$4 and linewidth	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
13	24	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same develop\$4) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical)) and ((second near12 (photoresist or resist) near6 (layer or coat\$4 or deposit\$4 or film)) and ((third or multiple) near9 (expos\$4 or irradiat\$4 or illuminat\$4)) and pitch\$4 and linewidth	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
14	2	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same develop\$4) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical)) and (second near12 (photoresist or resist)) and ((third or multiple) near9 (expos\$4 or irradiat\$4 or illuminat\$4)) and pitch\$4 and linewidth and ((design or programm\$6 or layout or data) same mask same (correct\$4 or subtract\$4))	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
15	7	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same develop\$4) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical)) and ((third or multiple) near9 (expos\$4 or irradiat\$4 or illuminat\$4)) and pitch\$4 and linewidth and ((design or programm\$6 or layout or data) same mask same (correct\$4 or subtract\$4))	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
16	21	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical or (direct near5 wrti\$4) or maskless)) and pitch\$4 and linewidth and ((imprint\$4 or ion\$3beam or e\$2beam or (electron near4 beam)) near5 (system or apparatus or module)) and (diffract\$4 near6 grat\$4) and (beam near6 split\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
17	21	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4)) same (mask or photomask or reticle or optical or (direct near5 wrti\$4) or maskless)) and pitch\$4 and linewidth and ((imprint\$4 or ion\$3beam or e\$2beam or (electron near4 beam)) near5 (system or apparatus or module)) and (diffract\$4 near26 grat\$4) and (beam near14 split\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
18	28	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4))) and pitch\$4 and linewidth and ((imprint\$4 or ion\$3beam or e\$2beam or (electron near4 beam)) near5 (system or apparatus or module)) and (diffract\$4 near26 grat\$4) and (beam near14 split\$4)	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	7	S18 NOT S16	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB